Title (en)

POWER DIODE STRUCTURE

Title (de)

LEISTUNGSDIODEN-STRUKTUR

Title (fr)

STRUCTURE DE DIODE DE PUISSANCE

Publication

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Application

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Abstract (en)

[origin: DE19823944A1] The invention relates to a power diode structure having improved dynamic characteristics which comprises a semiconductor body (1) of a first conduction type. A semiconductor zone (2) of the other conduction type which is contrary to the first conduction type is embedded in the one surface of said semiconductor body (1). The power diode also comprises an anode (4) which contacts the semiconductor zone (2), and has a cathode (5) which contacts the semiconductor body (1). At least one floating region (6) of the second conduction type is provided in the semiconductor body (1).

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IPC 8 full level

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